

Fabrication of superconducting NdFeAs(O,H) epitaxial thin films

*Keisuke Kondo¹, Seiya Motoki¹, Takafumi Hatano¹, Takahiro Urata¹, Kazumasa Iida^{1,2}, Hiroshi Ikuta¹

Department of Material Physics, Nagoya University, Japan¹
JST CREST, Japan²

$LnFeAs(O,F)$ (Ln : lanthanide) exhibits the highest superconducting transition temperature (T_c) up to 58 K among the Fe-based superconductors. However, the amount of F that can be substituted for O is limited to about 20% and it is difficult to investigate the physical properties in the overdoped region. On the other hand, Hanna *et al.* reported that the substitution limit can be increased to about 80% by changing the substituting elements from F to H[1]. Furthermore, SmFeAs(O,H) epitaxial thin films on MgO (001) substrates were grown recently using a topotactic reaction $SmFeAsO + (x/2)CaH_2 \rightarrow SmFeAs(O_{1-x}H_x) + (x/2)CaO$ [2]. It is interesting whether $LnFeAs(O,H)$ thin films for other Ln can be realized. Here, we report on the fabrication of NdFeAs(O,H) thin films using the same H doping method[2], and their structural and electro-magnetic properties.

Parent NdFeAsO thin films having a thickness of 20 - 30 nm were grown on MgO (001) substrates by molecular beam epitaxy[3]. The NdFeAsO film and CaH₂ powder were sealed in an evacuated quartz tube. The whole arrangement was then annealed under various conditions. Figure 1 (a) and (b) show the results of X-ray diffraction (XRD) measurement and the temperature dependence of resistance for one of the NdFeAs(O,H) films. For comparison, the data of an as-grown film are also shown. From the XRD measurements, no impurities were observed both for as-grown and annealed films. The 00 l peaks shifted to higher angles. The c -axis length changed from 8.587 Å to 8.466 Å. These results suggest that a phase-pure NdFeAs(O,H) film was obtained. The resistance measurement showed an onset T_c of 48 K and zero resistance at 45 K, respectively. The magnetization measurements exhibited a self-field critical current density of over 8 MA/cm² at 4 K, which is roughly comparable to our NdFeAs(O,F) films.

[1] T. Hanna *et al.*, *Phys. Rev. B* **84**, 024521 (2011). [2] J. Matsumoto *et al.*, arXiv:1903.11819 (2019). [3] T. Kawaguchi *et al.*, *Appl. Phys. Express* **4**, 083102 (2011).

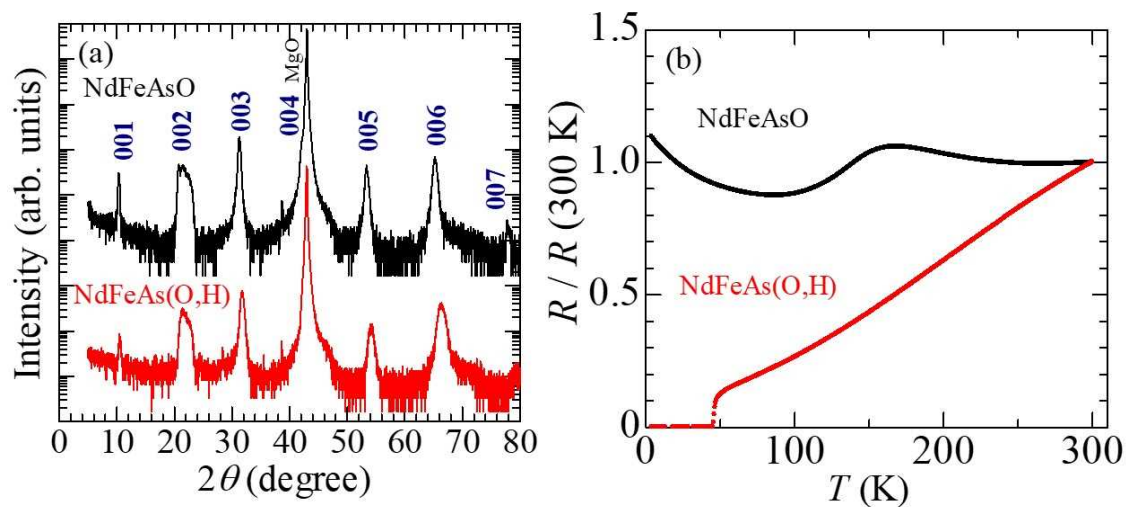


Fig.1. (a) XRD patterns and (b) the temperature dependence of resistance of non-doped and doped NdFeAs(O,H) thin films.

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